



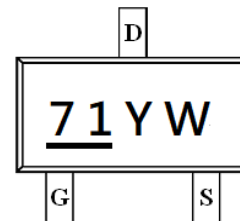
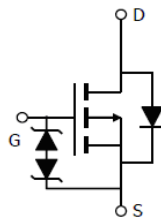
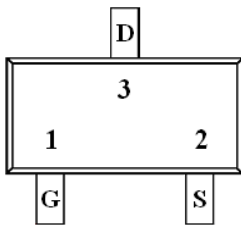
General Description

AFP7001, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge. These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- -60V/-0.5A, $R_{DS(ON)}=6\Omega@V_{GS}=-10V$
- -60V/-0.025A, $R_{DS(ON)}=10\Omega@V_{GS}=-4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- ESD Protection Diode design-in
- SOT-323 package design

Pin Description (SOT-323)



Application

- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Power Supply Converter Circuits
- Solid-State Relays

Pin Define

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP7001S32RG	71YW	SOT-323	Tape & Reel	3000 EA

- ※ 71 parts code
- ※ Y year code (0 ~ 9)
- ※ W week code (A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52)
- ※ AFP7001S32RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C	-0.185
		T _A =70°C	-0.115
Pulsed Drain Current	I _{DM}	-0.8	A
Power Dissipation	P _D	T _A =25°C	0.35
		T _A =70°C	0.14
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	120	°C/W

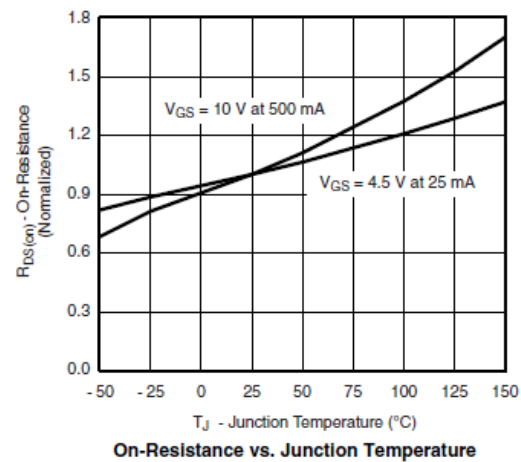
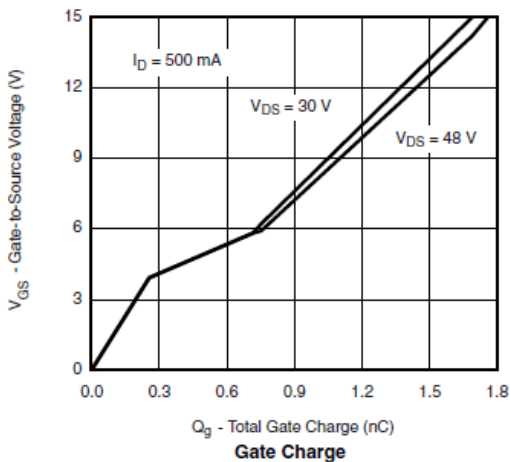
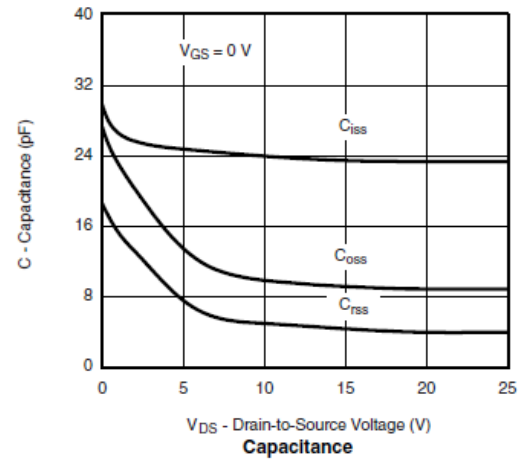
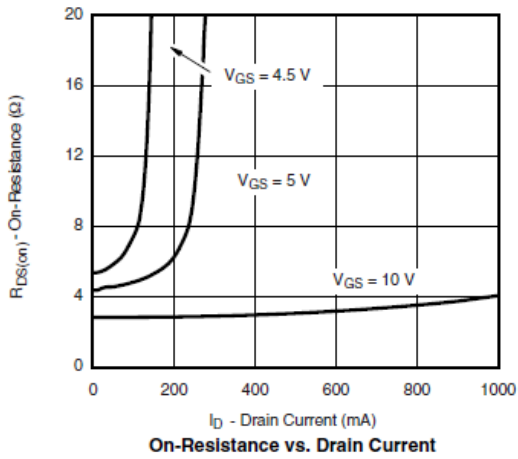
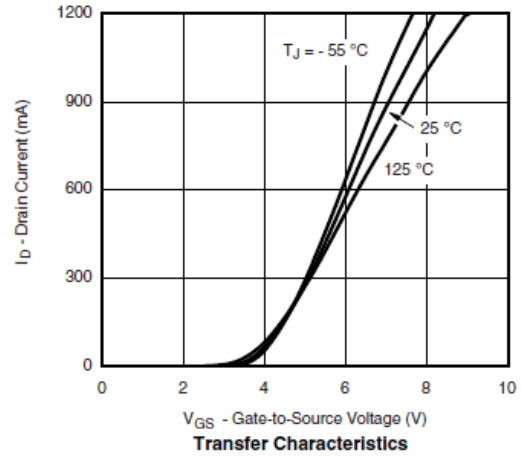
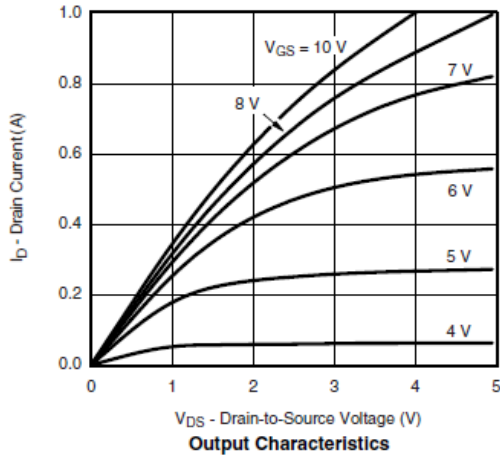
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250uA	-60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-1.0		-2.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±10	uA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-48V, V _{GS} =0V			-1	uA
		V _{DS} =-48V, V _{GS} =0V T _J =85°C			-30	
On-State Drain Current	I _{D(on)}	V _{DS} ≤ -10V, V _{GS} =-10V	-0.6			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-0.5A			6	Ω
		V _{GS} =-4.5V, I _D =-0.025A			10	
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-1.0A		2.8		S
Diode Forward Voltage	V _{SD}	I _S =-0.2A, V _{GS} =0V		-0.75	-1.4	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =-30V, V _{GS} =-15V I _D ≡-0.5A		2		nC
Gate-Source Charge	Q _{gs}			0.53		
Gate-Drain Charge	Q _{gd}			0.72		
Input Capacitance	C _{iss}	V _{DS} =-25V, V _{GS} =0V f=1MHz		25		pF
Output Capacitance	C _{oss}			13		
Reverse Transfer Capacitance	C _{rss}			7.3		
Turn-On Time	t _{d(on)}	V _{DD} =-25V, R _L =150Ω		20		ns
Turn-Off Time	t _{d(off)}	I _D ≡-0.2A, V _{GEN} =-10V, R _G =10Ω		35		

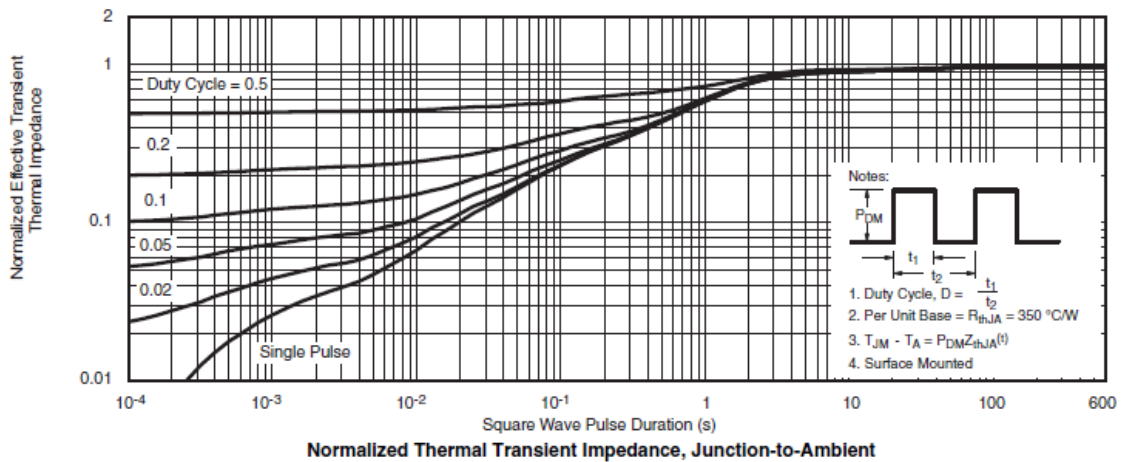
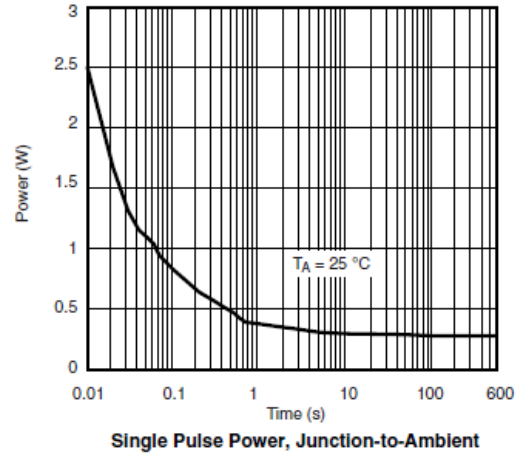
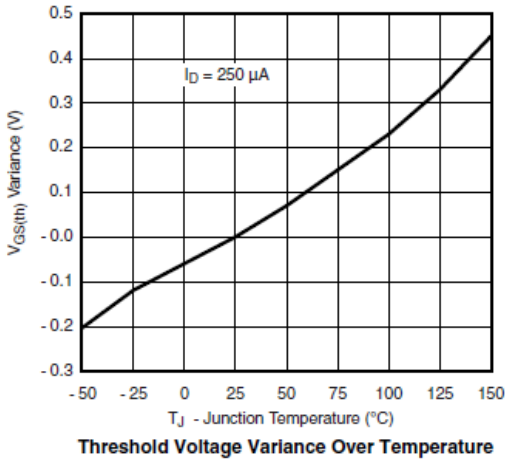
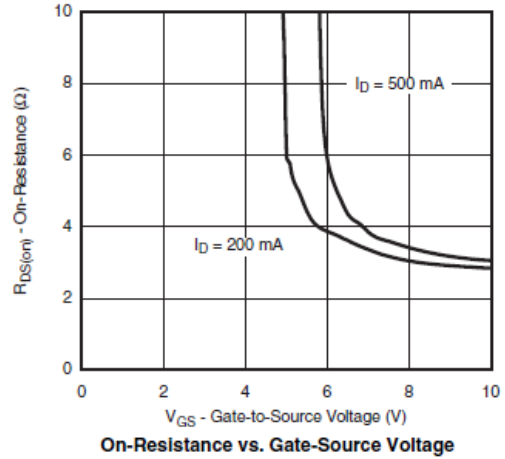
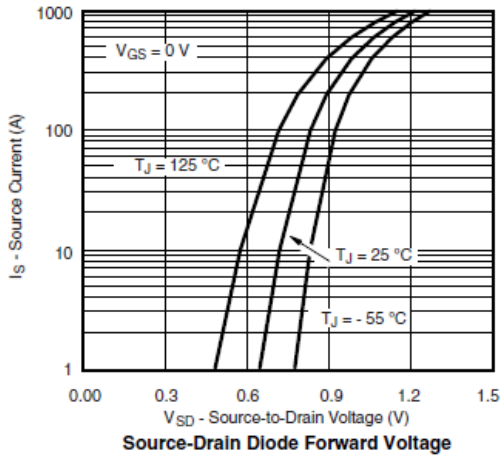


Typical Characteristics





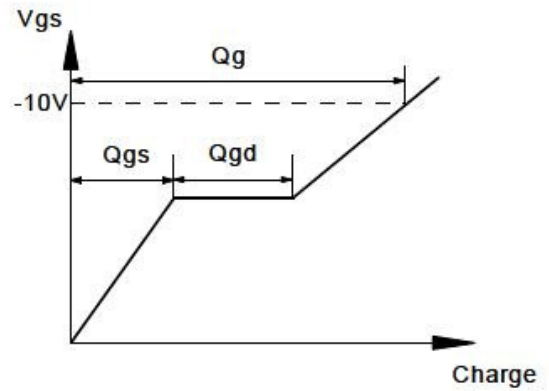
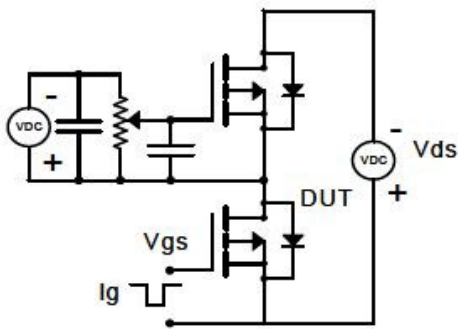
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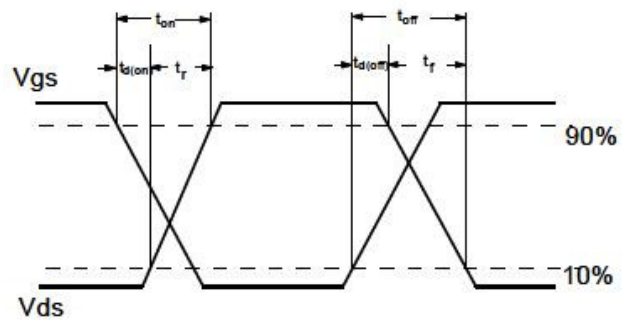
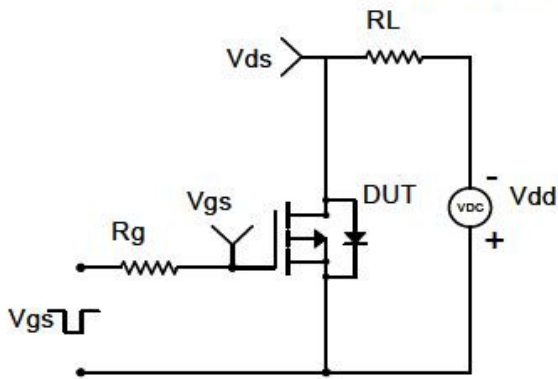


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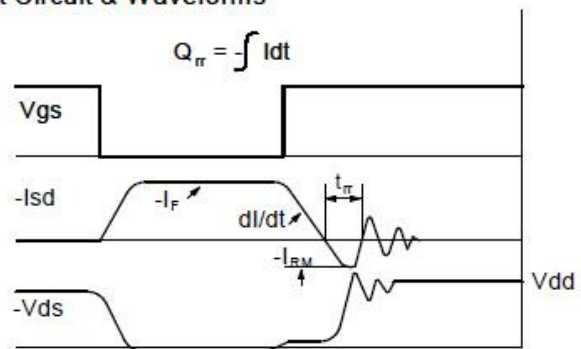
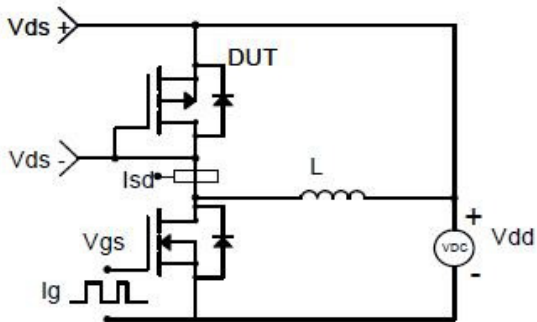
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

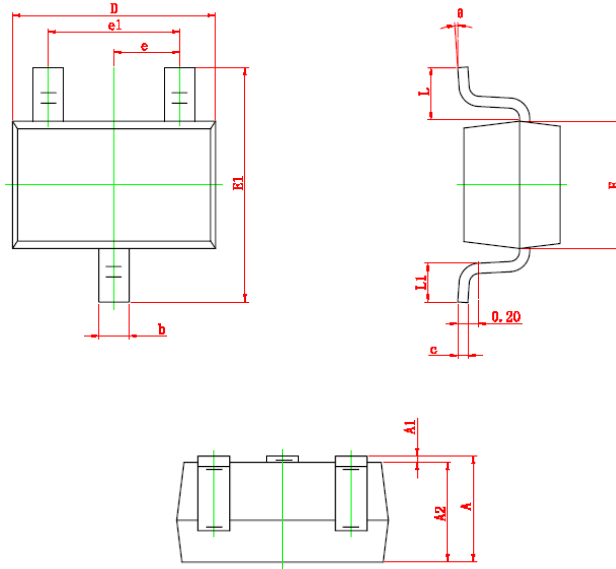


Diode Recovery Test Circuit & Waveforms





Package Information (SOT-323)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

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 2F, No.80, Sec.1, Cheng Kung Rd., Nan Kang Dist., Taipei City 115, Taiwan (R.O.C.)
 Tel : 886 2) 2651 3928
 Fax : 886 2) 2786 8483
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